

9 a memory coupled to the controller comprising a computer readable medium
10 having a computer readable program embodied therein for directing operation of the substrate
11 processing system, the computer readable program including a first set of computer
12 instructions for controlling the gas delivery system to flow selected deposition gases into the
13 process chamber at deposition gas flow rates, a second set of computer instructions for
14 controlling the gas delivery system to add a flow of an inert gas to the selected deposition
15 gases at a flow rate previously determined to achieve a desired low deposition rate from a
16 reaction of the selected deposition gases, the desired low deposition rate being lower than a
17 deposition rate using the selected deposition gases at the deposition gas flow rates with a lower
18 flow rate of the inert gas, and a third set of computer instructions for controlling the power
19 supply to supply power to the process chamber to react the deposition gases to deposit a film at
20 the low deposition rate.

REMARKS

Claims 1-10 and 44-54 are pending. Claim 1 has been amended and new claims 44-54 have been added. No new matter has been introduced.

Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 415-576-0200.

Respectfully submitted,



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